

2N3906 Transistors

Si PNP LP HF BJT

Military/High-Rel N

V(BR)CEO (V) 40

V(BR)CBO (V) 40

I(C) Max. (A) 200m

Absolute Max. Power Diss. (W) 350m

Maximum Operating Temp (θ C) 150 \bar{o}

I(CBO) Max. (A) 50n \bar{d}

@V(CBO) (V) (Test Condition) 30

h(FE) Min. Current gain. 100

h(FE) Max. Current gain. 300

@I(C) (A) (Test Condition) 10m

@V(CE) (V) (Test Condition) 1.0

f(T) Min. (Hz) Transition Freq 250M

@I(C) (A) (Test Condition) 10m

@V(CE) (V) (Test Condition) 20

V(CE)sat Max. (V) .40

@I(C) (A) (Test Condition) 50m

@I(B) (A) (Test Condition) 5.0m

h(fe) Min. SS Current gain. 2.5

@I(C) (A) (Test Condition) 10m

@V(CE) (V) (Test Condition) 20